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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	100
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 42x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dx256vlq10

Table of Contents

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB • 2M0 = 2 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105 • C = –40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm) • MJ = 256 MAPBGA (17 mm x 17 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MK20DN512ZVMD10

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. • V_{DD} slew rate ≥ 5.7 kV/s • V_{DD} slew rate < 5.7 kV/s	— —	300 1.7 V / (V_{DD} slew rate)	μs	1
	• VLLS1 → RUN	—	130	μs	
	• VLLS2 → RUN	—	92	μs	
	• VLLS3 → RUN	—	92	μs	
	• LLS → RUN	—	5.9	μs	
	• VLPS → RUN	—	5.0	μs	
	• STOP → RUN	—	5.0	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8V • @ 3.0V	— —	37 38	63 64	mA mA	2

I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash
	• @ 1.8V
	• @ 3.0V
	  • @ 25°C
	  • @ 125°C
		—
		—
		—
			46
			47
			58
				77
				63
				79
					mA
					mA
					mA
						3, 4

I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	20	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	9	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	1.12	—	mA	6

Table continues on the next page...

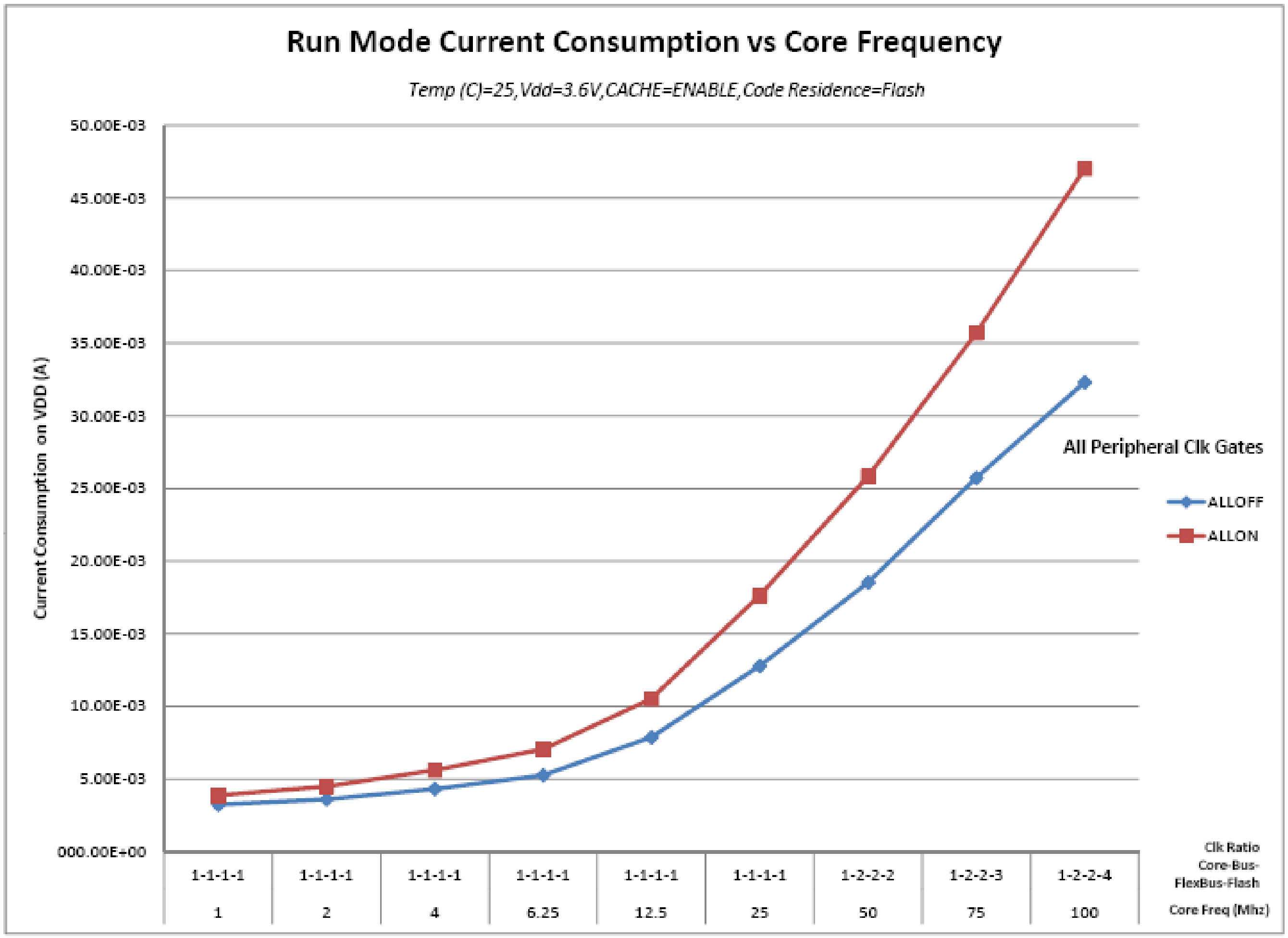

Figure 2. Run mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 144LQFP and 144MAPBGA

Symbol	Description	Frequency band (MHz)	144LQFP	144MAPBGA	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	23	12	dBμV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	27	24	dBμV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	28	27	dBμV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	14	11	dBμV	
V_{RE_IEC}	IEC level	0.15–1000	K	K	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 96 MHz, f_{BUS} = 48 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	100	MHz	
f_{SYS_USB}	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{BUS}	Bus clock	—	50	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
FB_CLK	FlexBus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	

Table continues on the next page...

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f_{ERCLK}	External reference clock	—	16	MHz	
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
$f_{FlexCAN\_ERCLK}$	FlexCAN external reference clock	—	8	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CAN, CMT, and I²C signals.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	16	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select ($\overline{EZP\_CS}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength)				4
	• Slew disabled				
	• $1.71 \leq V_{DD} \leq 2.7V$	—	12	ns	
	• $2.7 \leq V_{DD} \leq 3.6V$	—	6	ns	
	• Slew enabled				
	• $1.71 \leq V_{DD} \leq 2.7V$	—	36	ns	
	• $2.7 \leq V_{DD} \leq 3.6V$	—	24	ns	

Table continues on the next page...

Table 13. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	20	—	ns
	• Serial Wire Debug	10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	$\overline{TRST}$ assert time	100	—	ns
J14	$\overline{TRST}$ setup time (negation) to TCLK high	8	—	ns

Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	20	
	• Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns

Table continues on the next page...

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 20. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk256k}$	Erase Block high-voltage time for 256 KB	—	104	904	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 21. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk256k}$	Read 1s Block execution time • 256 KB program/data flash	—	—	1.7	ms	
$t_{rd1sec2k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
$t_{ersblk256k}$	Erase Flash Block execution time • 256 KB program/data flash	—	122	985	ms	2
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
$t_{pgmsec512}$ $t_{pgmsec1k}$ $t_{pgmsec2k}$	Program Section execution time • 512 bytes flash • 1 KB flash • 2 KB flash	— — —	2.4 4.7 9.3	— — —	ms ms ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	250	2000	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

Table continues on the next page...

6.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the flash memory module to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

$$\text{Writes\_subsystem} = \frac{\text{EEPROM} - 2 \times \text{EEESPLIT} \times \text{EEESIZE}}{\text{EEESPLIT} \times \text{EEESIZE}} \times \text{Write\_efficiency} \times n_{nvmcycd}$$

where

- Writes_subsystem — minimum number of writes to each FlexRAM location for subsystem (each subsystem can have different endurance)
- EEPROM — allocated FlexNVM for each EEPROM subsystem based on DEPART; entered with the Program Partition command
- EEESPLIT — FlexRAM split factor for subsystem; entered with the Program Partition command
- EEESIZE — allocated FlexRAM based on DEPART; entered with the Program Partition command
- Write_efficiency —
    - 0.25 for 8-bit writes to FlexRAM
    - 0.50 for 16-bit or 32-bit writes to FlexRAM
- $n_{nvmcycd}$ — data flash cycling endurance (the following graph assumes 10,000 cycles)

Table 28. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.

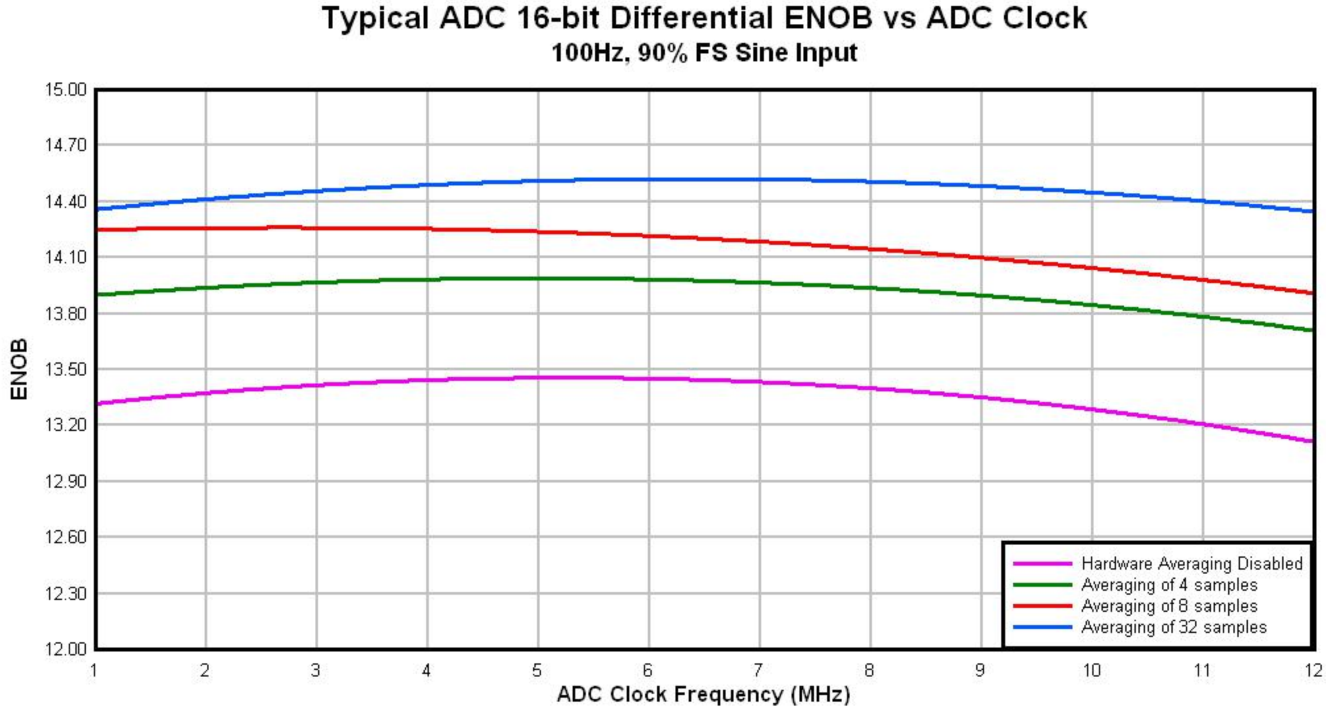

Figure 14. Typical ENOB vs. ADC_CLK for 16-bit differential mode

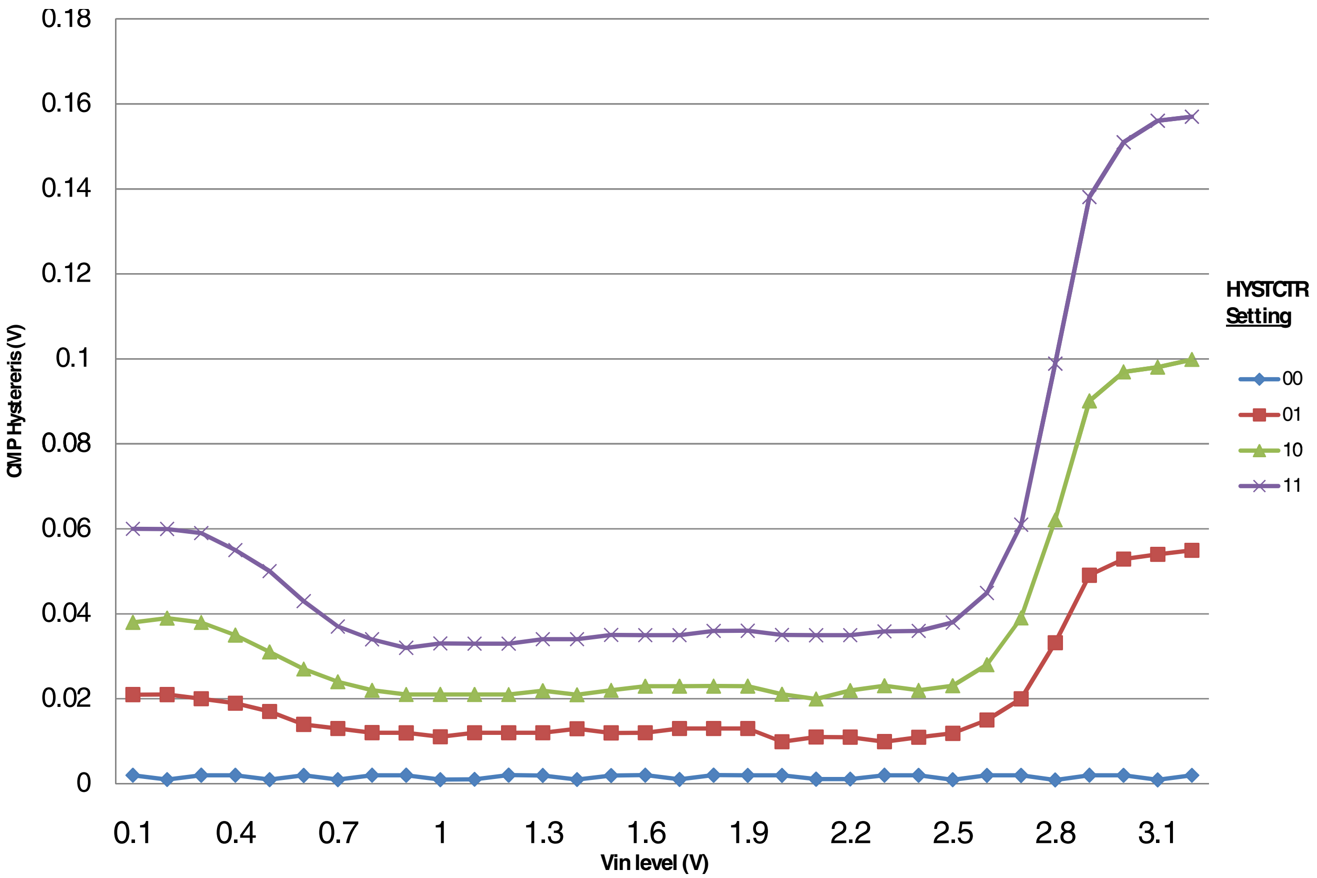

Figure 17. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=1)

6.6.3 12-bit DAC electrical characteristics

6.6.3.1 12-bit DAC operating requirements

Table 32. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or the voltage output of the VREF module (VREF_OUT)
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit **usb.org**.

6.8.2 USB DCD electrical specifications

Table 38. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DP_SRC}	USB_DP source voltage (up to 250 μA)	0.5	—	0.7	V
V_{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I_{DP_SRC}	USB_DP source current	7	10	13	μA
I_{DM_SINK}	USB_DM sink current	50	100	150	μA
R_{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	kΩ
V_{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

6.8.3 USB VREG electrical specifications

Table 39. USB VREG electrical specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I_{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	—	120	186	μA	
I_{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	μA	
I_{DDoff}	Quiescent current — Shutdown mode • VREGIN = 5.0 V and temperature=25 °C • Across operating voltage and temperature	— —	650 —	— 4	nA μA	
$I_{LOADrun}$	Maximum load current — Run mode	—	—	120	mA	
$I_{LOADstby}$	Maximum load current — Standby mode	—	—	1	mA	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) > 3.6 V • Run mode • Standby mode	3 2.1	3.3 2.8	3.6 3.6	V V	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C_{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	

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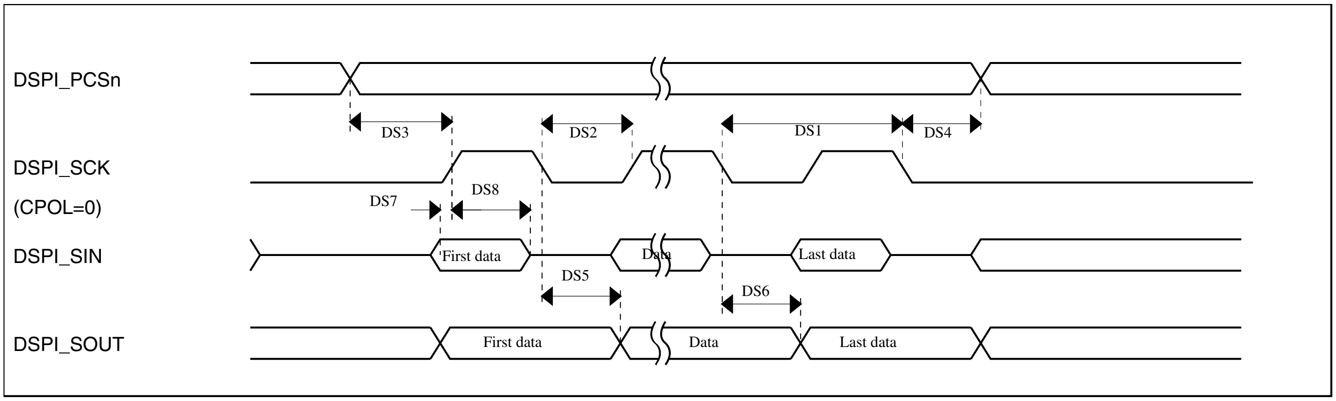

Figure 20. DSPI classic SPI timing — master mode

Table 41. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz
DS9	DSPI_SCK input cycle time	4 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	14	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	14	ns

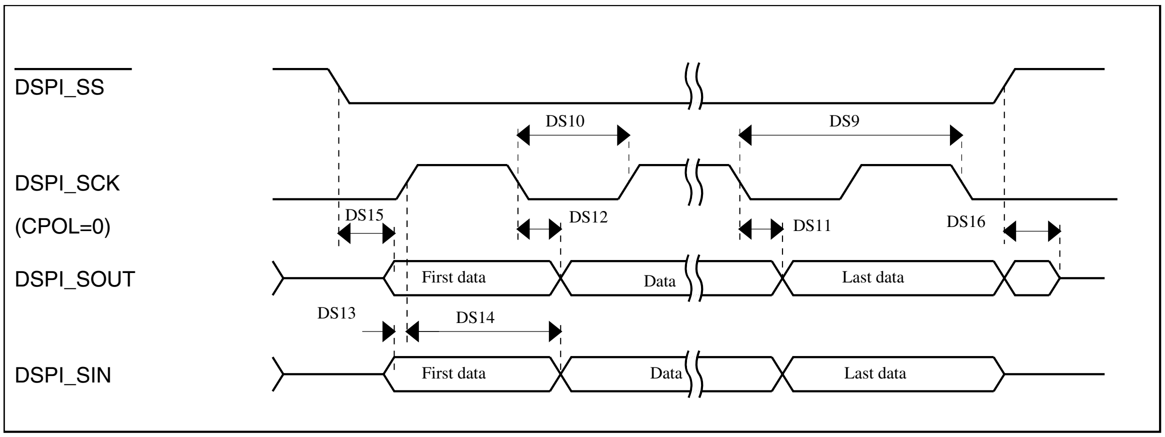

Figure 21. DSPI classic SPI timing — slave mode

6.8.6 DSPI switching specifications (full voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 42. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	—	12.5	MHz	
DS1	DSPI_SCK output cycle time	4 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2) - 4$	$(t_{SCK/2}) + 4$	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	$(t_{BUS} \times 2) - 4$	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	$(t_{BUS} \times 2) - 4$	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-1.2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	19.1	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

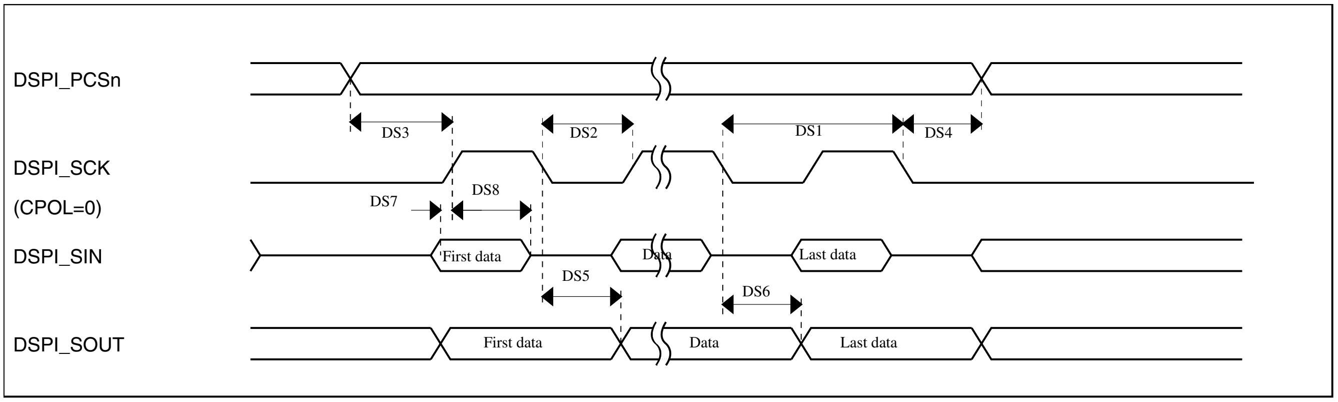

Figure 22. DSPI classic SPI timing — master mode

Table 43. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz

Table continues on the next page...

Table 43. Slave mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 4$	$(t_{SCK/2}) + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	24	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	3.2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	19	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

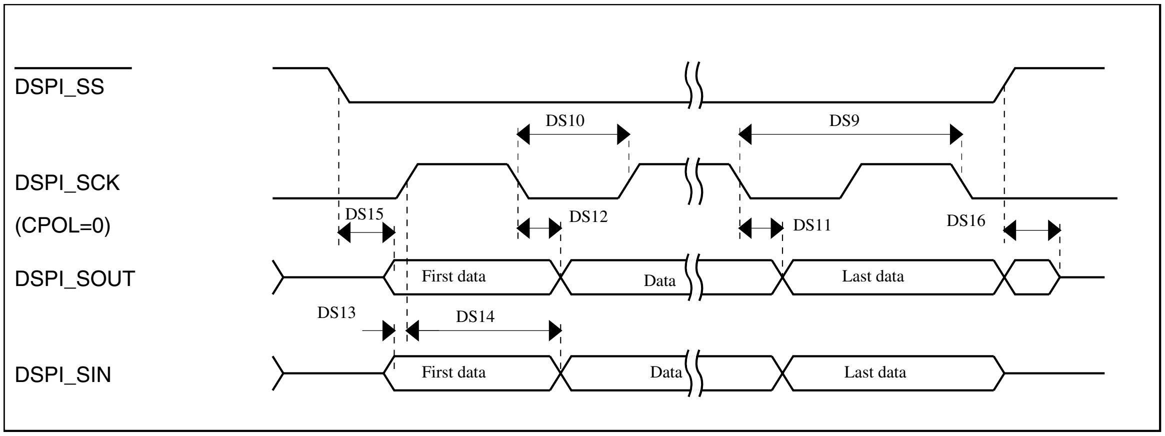

Figure 23. DSPI classic SPI timing — slave mode

6.8.7 Inter-Integrated Circuit Interface (I^2C) timing

Table 44. I^2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.3	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs
Data hold time for I_2C bus devices	t_{HD}; DAT	0[1]	3.45[2]	0[3]	0.9[1]	µs
Data set-up time	t_{SU}; DAT	250[4]	—	100[2, 5]	—	ns
Rise time of SDA and SCL signals	t_r	—	1000	$20 + 0.1C_b$[6]	300	ns

Table continues on the next page...

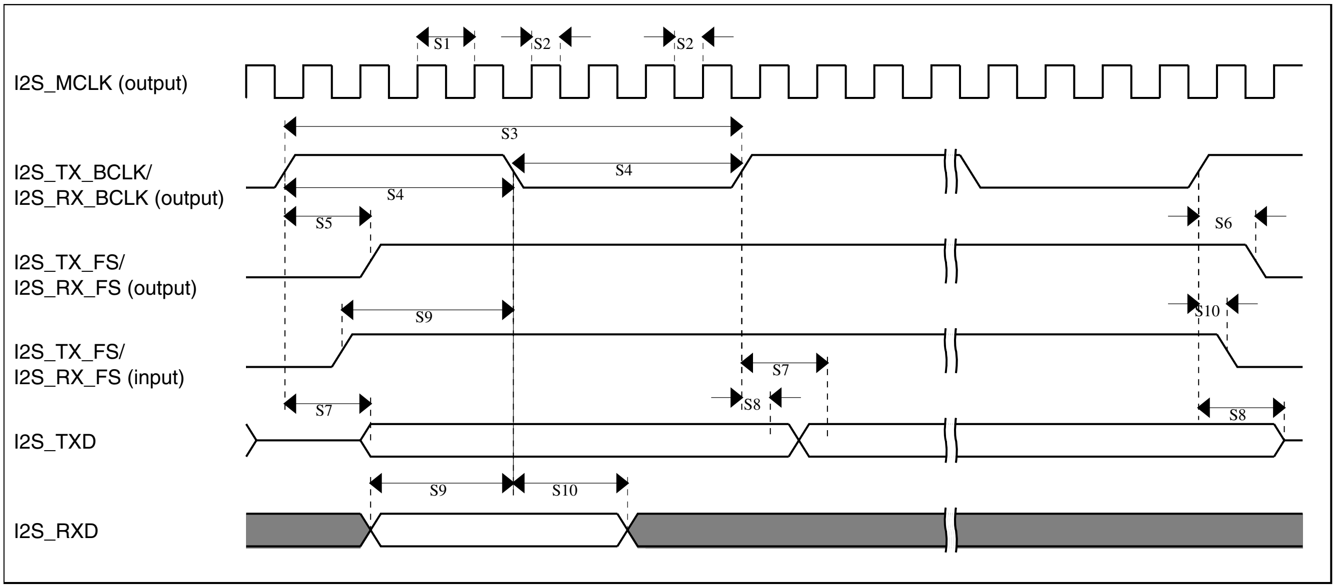

Figure 30. I2S/SAI timing — master modes

Table 51. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	3	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	63	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

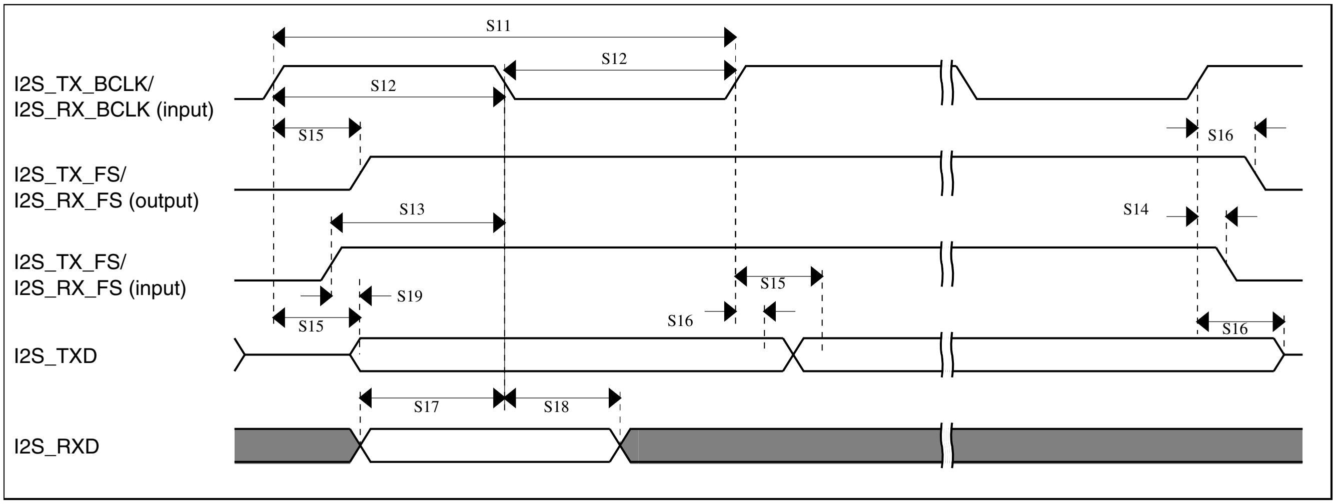

Figure 31. I2S/SAI timing — slave modes

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 52. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	8	15	MHz	2, 3
f_{ELEmax}	Electrode oscillator frequency	—	1	1.8	MHz	2, 4
C_{REF}	Internal reference capacitor	—	1	—	pF	
V_{DELTA}	Oscillator delta voltage	—	500	—	mV	2, 5
I_{REF}	Reference oscillator current source base current • 2 µA setting (REFCHRG = 0) • 32 µA setting (REFCHRG = 15)	 — —	 2 36	 3 50	µA	2, 6
I_{ELE}	Electrode oscillator current source base current • 2 µA setting (EXTCHRG = 0) • 32 µA setting (EXTCHRG = 15)	 — —	 2 36	 3 50	µA	2, 7
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	—	fF/count	11
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	µs	12
I_{TSI_RUN}	Current added in run mode	—	55	—	µA	
I_{TSI_LP}	Low power mode current adder	—	1.3	2.5	µA	13

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. Fixed external capacitance of 20 pF.
3. REFCHRG = 2, EXTCHRG=0.
4. REFCHRG = 0, EXTCHRG = 10.
5. V_{DD} = 3.0 V.
6. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
7. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
8. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; Iext = 16.
9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; Iext = 16.
10. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; Iext = 16.
11. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes. Sensitivity depends on the configuration used. The documented values are provided as examples calculated for a specific configuration of operating conditions using the following equation: $(C_{ref} * I_{ext})/(I_{ref} * PS * NSCN)$

    The typical value is calculated with the following configuration:

    $I_{ext} = 6$ µA (EXTCHRG = 2), PS = 128, NSCN = 2, $I_{ref} = 16$ µA (REFCHRG = 7), C_{ref} = 1.0 pF

    The minimum value is calculated with the following configuration:

    $I_{ext} = 2$ µA (EXTCHRG = 0), PS = 128, NSCN = 32, $I_{ref} = 32$ µA (REFCHRG = 15), C_{ref} = 0.5 pF

    The highest possible sensitivity is the minimum value because it represents the smallest possible capacitance that can be measured by a single count.
12. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, EXTCHRG = 7.
13. REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
144-pin LQFP	98ASS23177W
144-pin MAPBGA	98ASA00222D

8 Pinout

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
48	J4	PTE27	DISABLED		PTE27		UART4_RTS_b					
49	H4	PTE28	DISABLED		PTE28							
50	J5	PTA0	JTAG_TCLK/SWD_CLK/EZP_CLK	TSI0_CH1	PTA0	UART0_CTS_b/UART0_COL_b	FTM0_CH5				JTAG_TCLK/SWD_CLK	EZP_CLK
51	J6	PTA1	JTAG_TDI/EZP_DI	TSI0_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
52	K6	PTA2	JTAG_TDO/TRACE_SWO/EZP_DO	TSI0_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/TRACE_SWO	EZP_DO
53	K7	PTA3	JTAG_TMS/SWD_DIO	TSI0_CH4	PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/SWD_DIO	
54	L7	PTA4/LLWU_P3	NMI_b/EZP_CS_b	TSI0_CH5	PTA4/LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
55	M8	PTA5	DISABLED		PTA5	USB_CLKIN	FTM0_CH2		CMP2_OUT	I2S0_TX_BCLK	JTAG_TRST_b	
56	E7	VDD	VDD	VDD								
57	G7	VSS	VSS	VSS								
58	J7	PTA6	DISABLED		PTA6		FTM0_CH3				TRACE_CLKOUT	
59	J8	PTA7	ADC0_SE10	ADC0_SE10	PTA7		FTM0_CH4				TRACE_D3	
60	K8	PTA8	ADC0_SE11	ADC0_SE11	PTA8		FTM1_CH0			FTM1_QD_PHA	TRACE_D2	
61	L8	PTA9	DISABLED		PTA9		FTM1_CH1			FTM1_QD_PHB	TRACE_D1	
62	M9	PTA10	DISABLED		PTA10		FTM2_CH0			FTM2_QD_PHA	TRACE_D0	
63	L9	PTA11	DISABLED		PTA11		FTM2_CH1			FTM2_QD_PHB		
64	K9	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD0	FTM1_QD_PHA	
65	J9	PTA13/LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_PHB	
66	L10	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_BCLK	I2S0_TXD1	
67	L11	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
68	K10	PTA16	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b/UART0_COL_b			I2S0_RX_FS	I2S0_RXD1	
69	K11	PTA17	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_RTS_b			I2S0_MCLK		
70	E8	VDD	VDD	VDD								
71	G8	VSS	VSS	VSS								
72	M12	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				

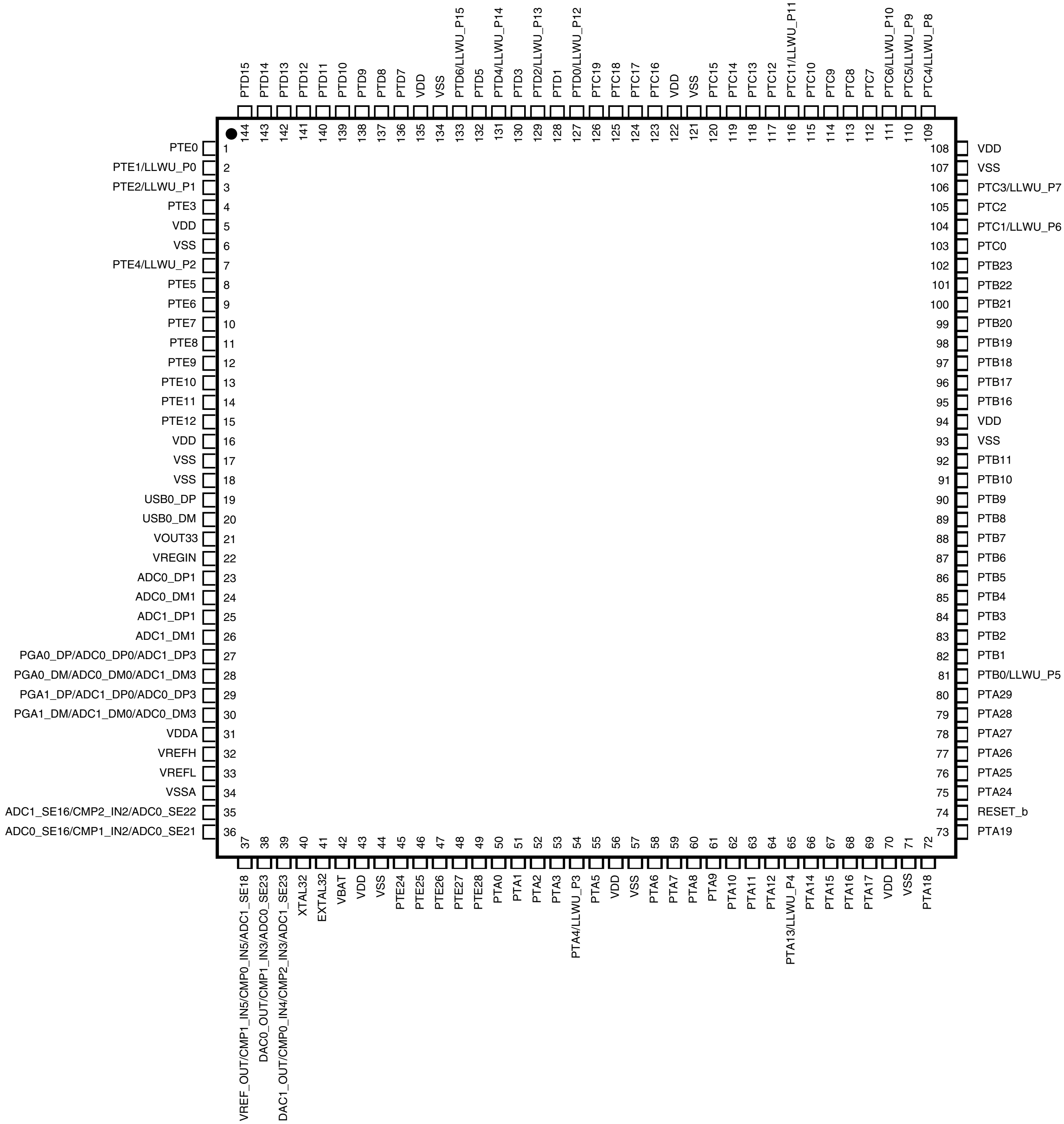

Figure 32. K20 144 LQFP Pinout Diagram